Device Modeling Report

COMPONENTS: Power MOSFET (Professional Model)
PART NUMBER: 2SJ651
MANUFACTURER: SANYO
Body Diode (Professional Model) / ESD Protection Diode

Bee Technologies Inc.

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MOSFET MODEL

PSpice model parameter	Model description
LEVEL	
L	Channel Length
W	Channel Width
KP	Transconductance
RS	Source Ohmic Resistance
RD	Ohmic Drain Resistance
VTO	Zero-bias Threshold Voltage
RDS	Drain-Source Shunt Resistance
TOX	Gate Oxide Thickness
CGSO	Zero-bias Gate-Source Capacitance
CGDO	Zero-bias Gate-Drain Capacitance
CBD	Zero-bias Bulk-Drain Junction Capacitance
MJ	Bulk Junction Grading Coefficient
PB	Bulk Junction Potential
FC	Bulk Junction Forward-bias Capacitance Coefficient
RG	Gate Ohmic Resistance
IS	Bulk Junction Saturation Current
N	Bulk Junction Emission Coefficient
RB	Bulk Series Resistance
PHI	Surface Inversion Potential
GAMMA	Body-effect Parameter
DELTA	Width effect on Threshold Voltage
ETA	Static Feedback on Threshold Voltage
THETA	Mobility Modulation
KAPPA	Saturation Field Factor
VMAX	Maximum Drift Velocity of Carriers
XJ	Metallurgical Junction Depth
UO	Surface Mobility

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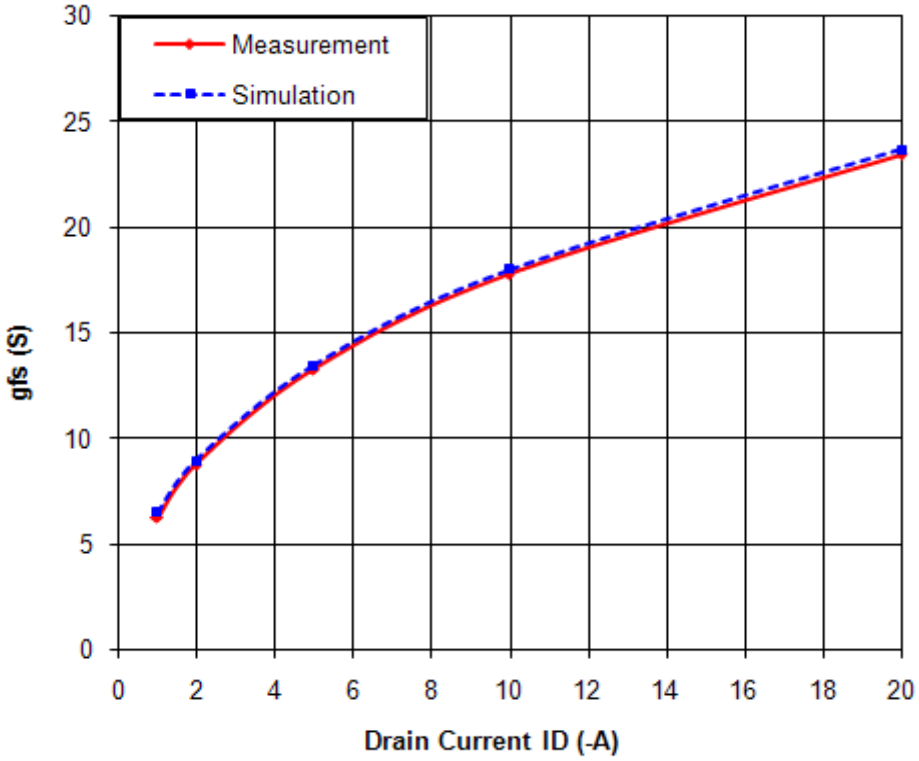
Transconductance Characteristic

Circuit Simulation Result



Comparison table

-Id(A)	gfs(S)		Error (%)
	Measurement	Simulation	
1	6.250	6.485	3.76
2	8.750	8.932	2.08
5	13.250	13.423	1.31
10	17.750	17.984	1.32
20	23.400	23.670	1.15

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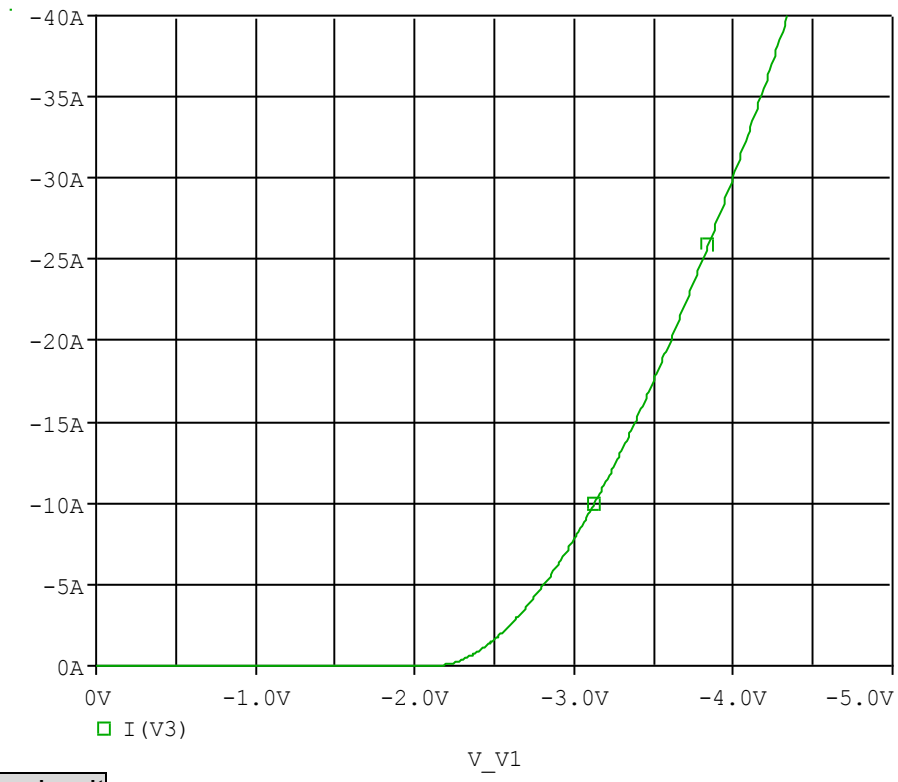
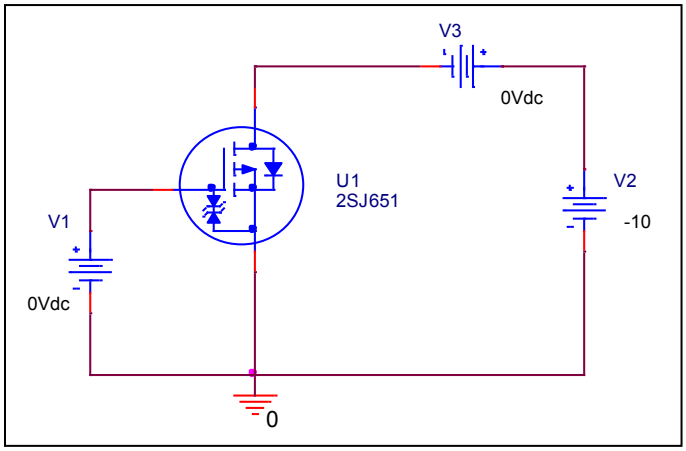
Vgs-Id Characteristic

Circuit Simulation result



Evaluation circuit



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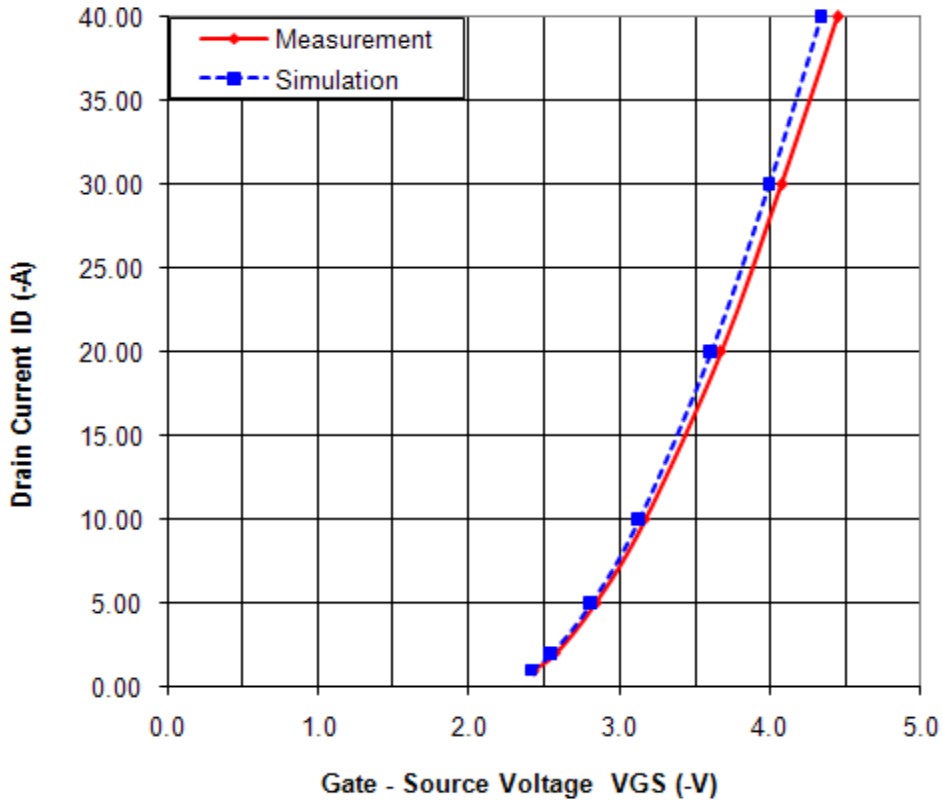
Comparison Graph

Circuit Simulation Result



Simulation Result

$-I_D$(mA)	$-V_{GS}$(V)		Error (%)
	Measurement	Simulation	
1	2.430	2.415	-0.62
2	2.570	2.545	-0.97
5	2.840	2.812	-0.99
10	3.170	3.129	-1.29
20	3.675	3.607	-1.85
30	4.075	3.997	-1.91
40	4.450	4.341	-2.45

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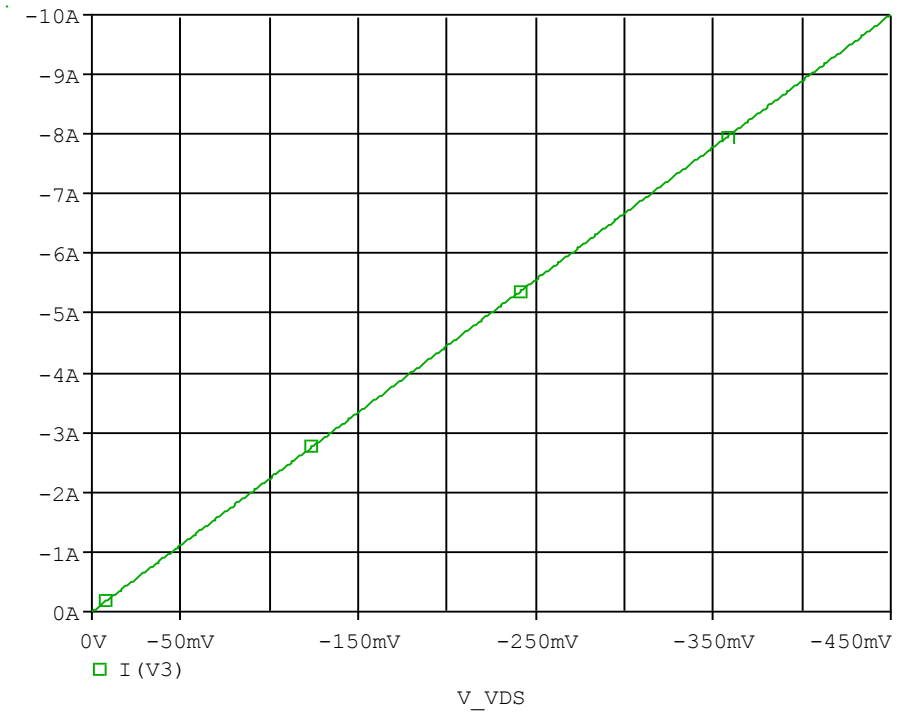
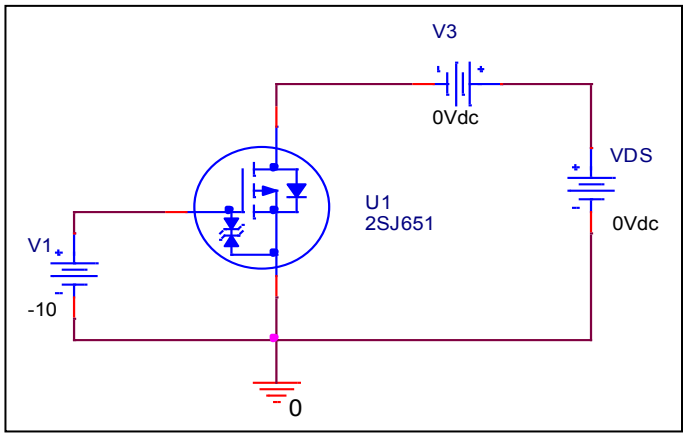
Rds(on) Characteristic

Circuit Simulation result



Evaluation circuit



Simulation Result

I_D= -10A, V_{GS}= -10V		Measurement	Simulation	Error (%)
R_{DS} (on)	mΩ	45.000	45.000	0.00

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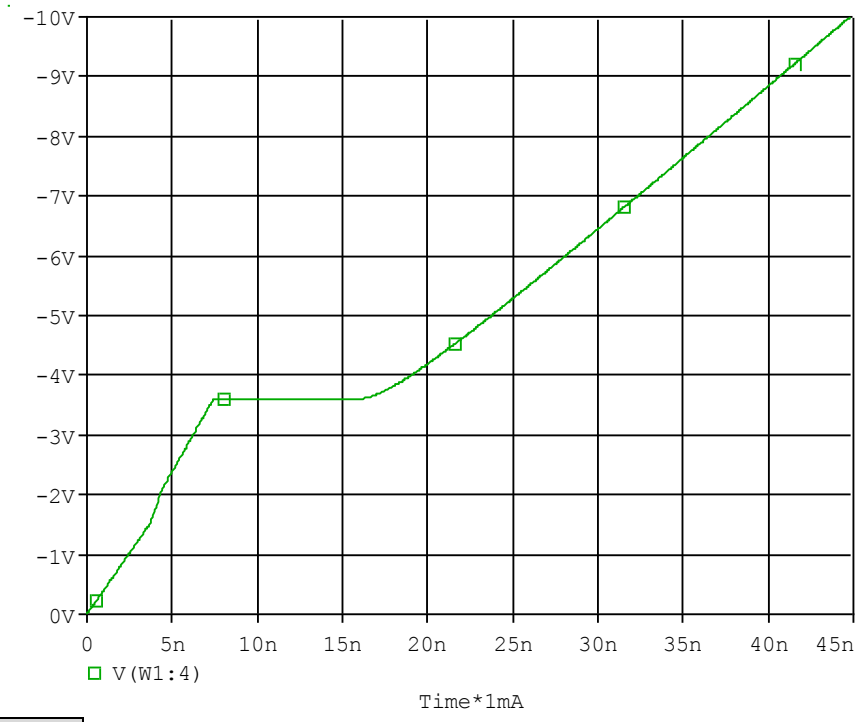
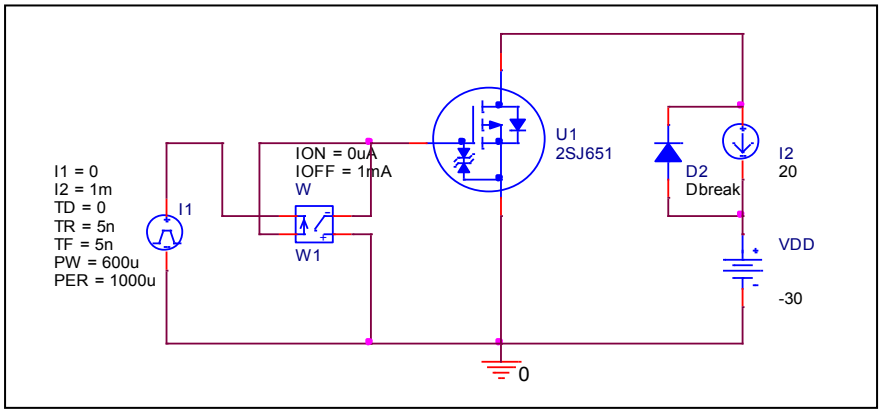
Gate Charge Characteristic

Circuit Simulation result



Evaluation circuit



Simulation Result

V_{DD}= -30V,I_D= -20A ,V_{GS}= -10V		Measurement	Simulation	Error (%)
Qgs	nC	7.400	7.412	0.16
Qgd	nC	9.000	9.087	0.97
Qg	nC	45.000	44.804	-0.44

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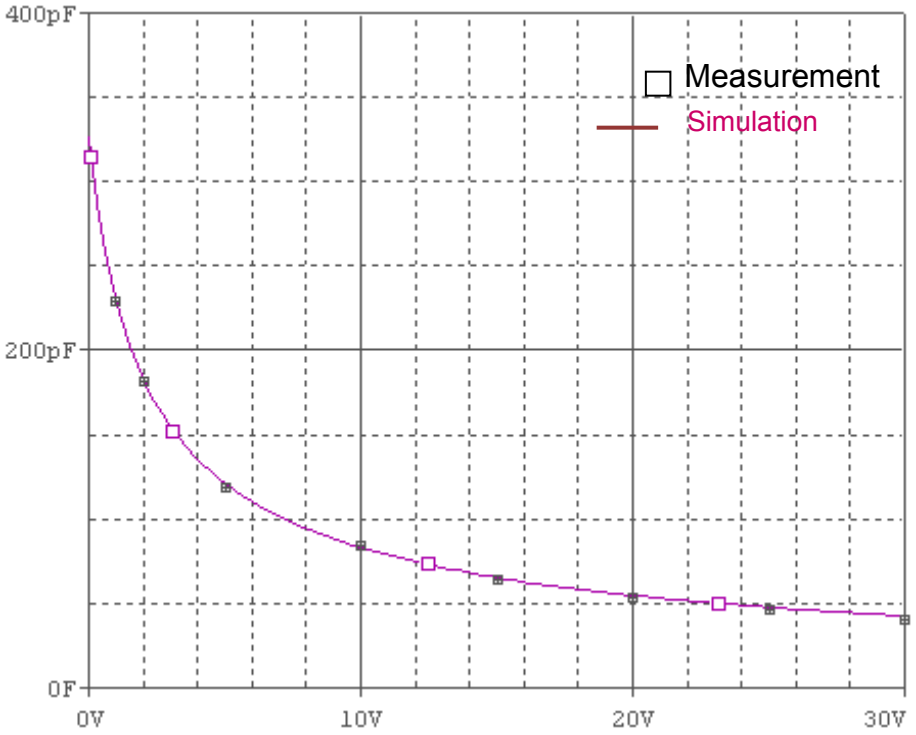
Capacitance Characteristic



Simulation Result

V_{SD}(V)	Cbd(pF)		Error(%)
	Measurement	Simulation	
1.0	230.000	230.000	0.00
2.0	183.000	182.700	-0.16
5.0	120.000	121.000	0.83
10.0	83.000	82.500	-0.60
15.0	65.000	65.600	0.92
20.0	55.000	54.750	-0.45
25.0	47.000	47.400	0.85
30.0	42.000	42.400	0.95

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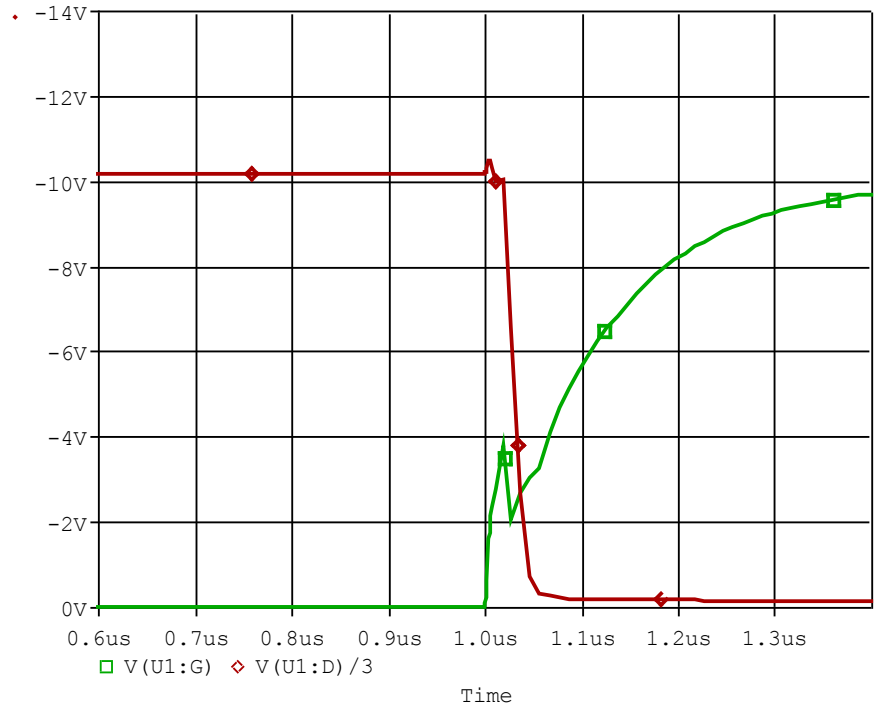
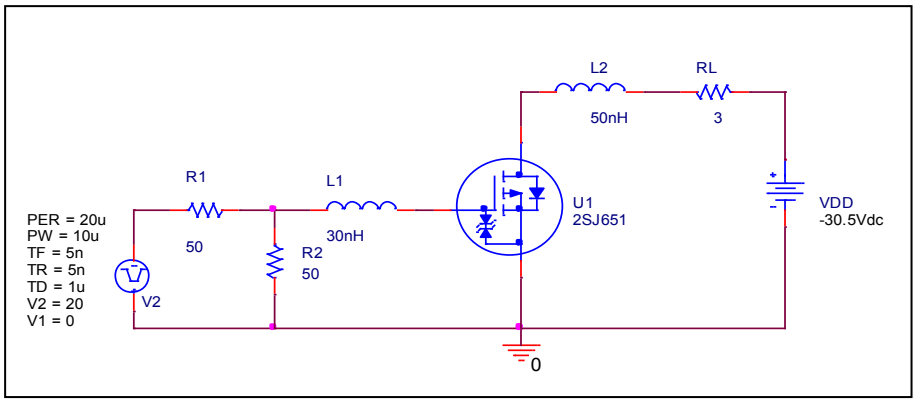
Switching Time Characteristic

Circuit Simulation result



Evaluation circuit



Simulation Result

I_D= -10A, V_{DD}= -30V V_{GS}=0/-10V		Measurement	Simulation	Error(%)
td(on)	ns	18.000	18.061	0.34

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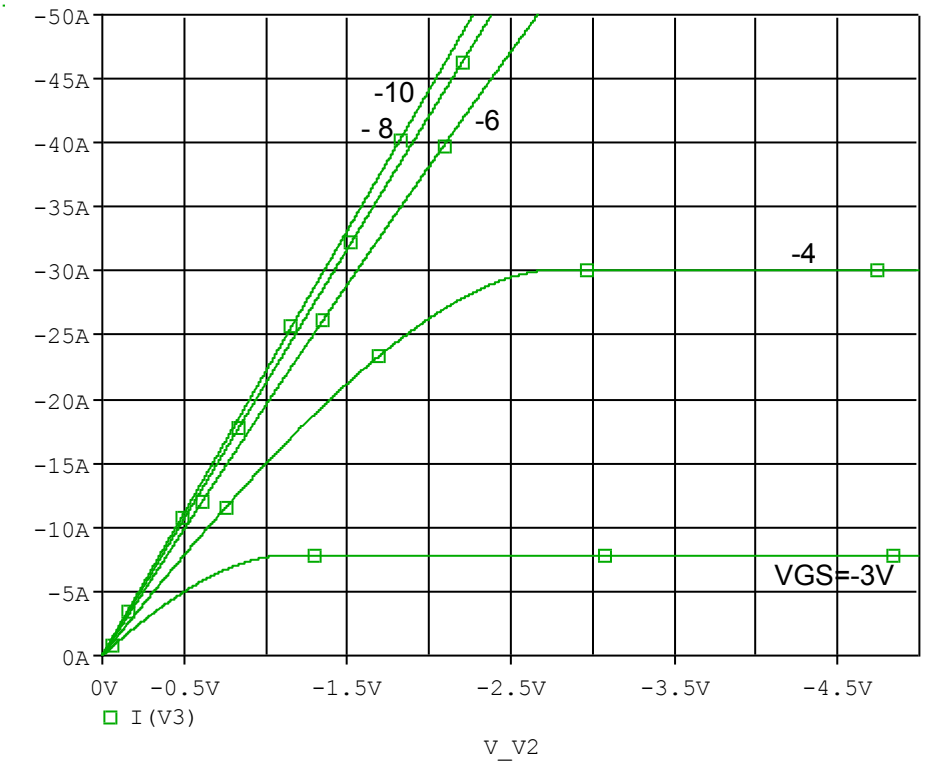
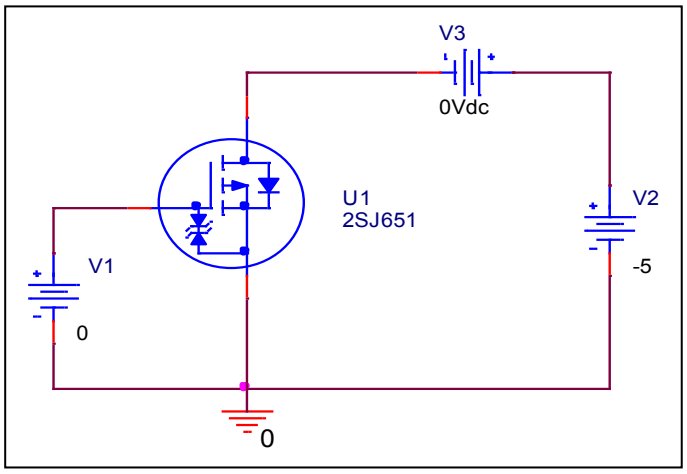
Output Characteristic

Circuit Simulation result



Evaluation circuit



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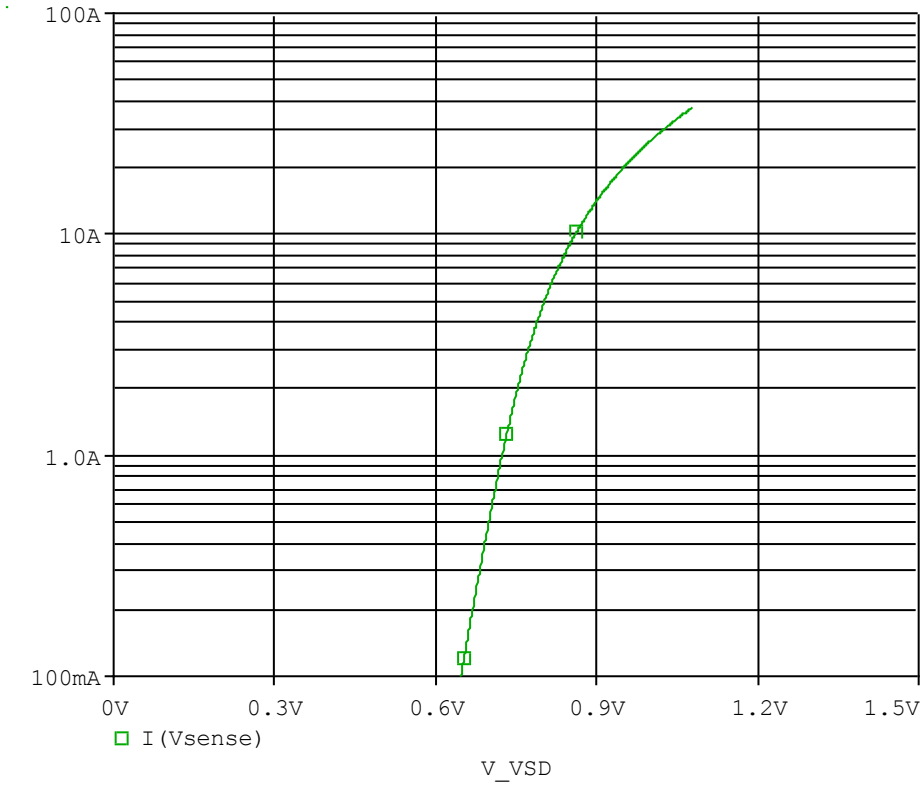
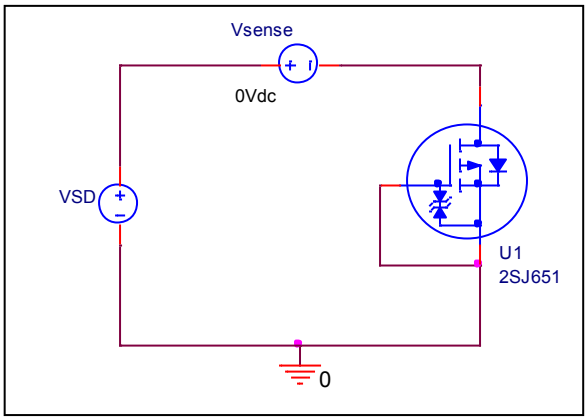
BODY DIODE SPICE MODEL
Forward Current Characteristic

Circuit Simulation Result



Evaluation Circuit



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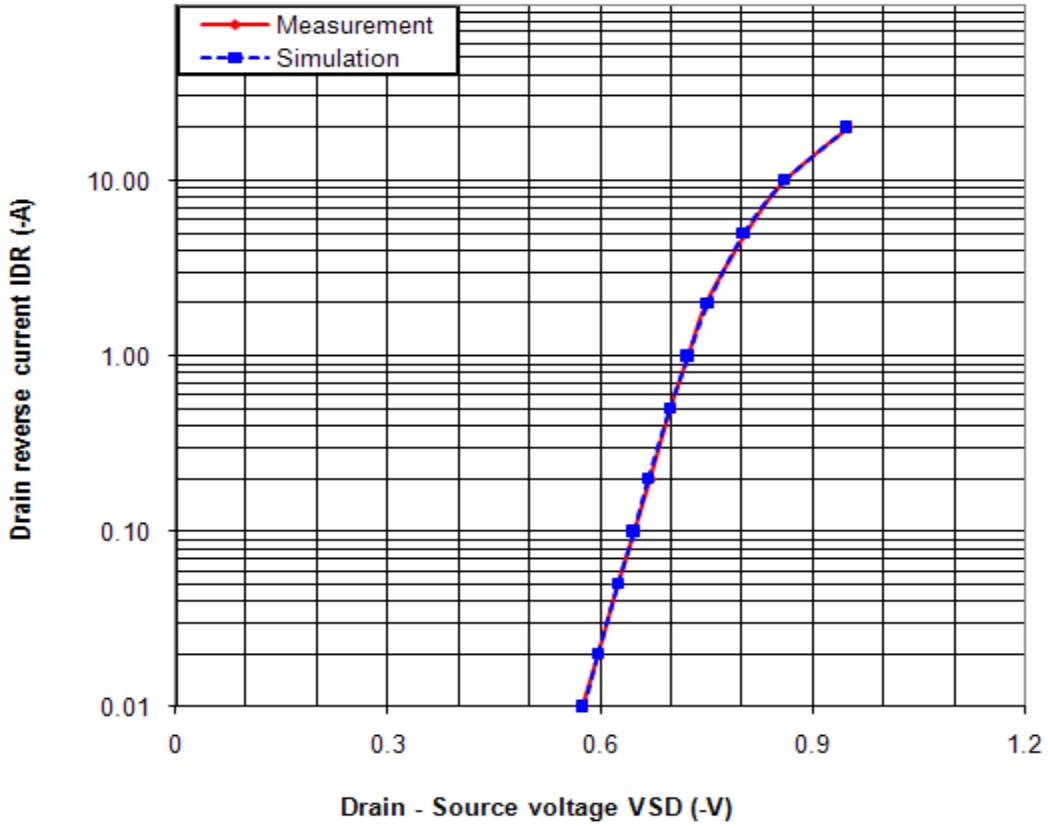
Comparison Graph

Circuit Simulation Result



Simulation Result

IDR(-A)	VSD (-V)		%Error
	Measurement	Simulation	
0.01	0.575	0.576	0.17
0.02	0.598	0.597	-0.17
0.05	0.625	0.626	0.10
0.10	0.648	0.647	-0.15
0.20	0.671	0.669	-0.30
0.50	0.700	0.699	-0.14
1.00	0.723	0.724	0.14
2.00	0.750	0.752	0.27
5.00	0.805	0.803	-0.25
10.00	0.860	0.860	0.05
20.00	0.950	0.949	-0.11

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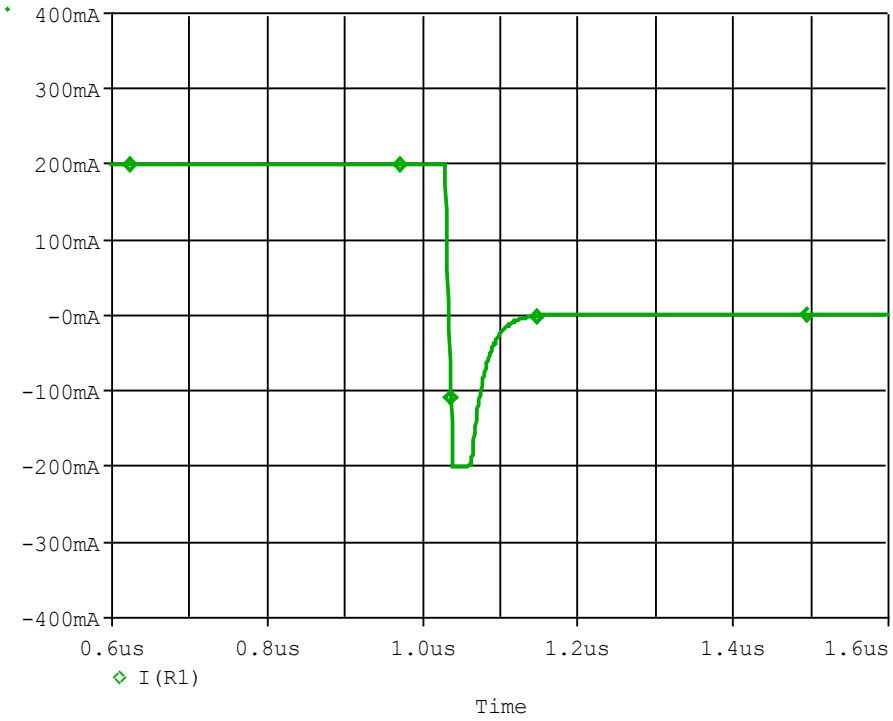
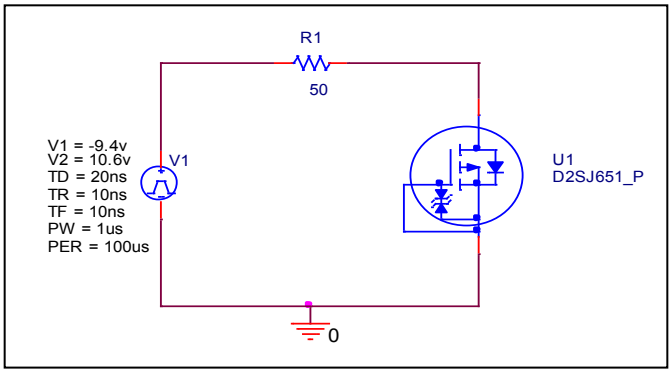
Reverse Recovery Characteristic

Circuit Simulation Result



Evaluation Circuit



Compare Measurement vs. Simulation

		Measurement	Simulation	Error (%)
trj	**ns**	**26.000**	**26.258**	**0.99**
trb	**ns**	**44.000**	**43.938**	**-0.14**
trr	**ns**	**70.000**	**70.196**	**0.28**

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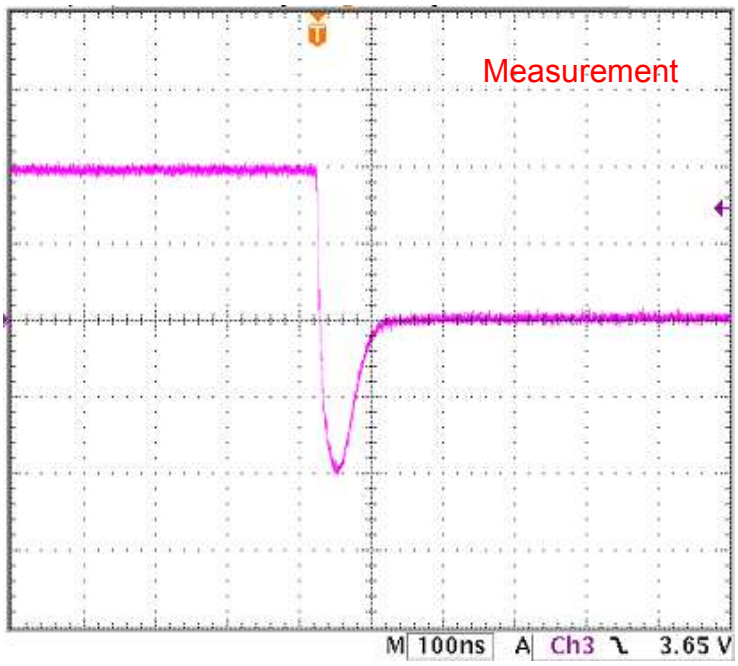
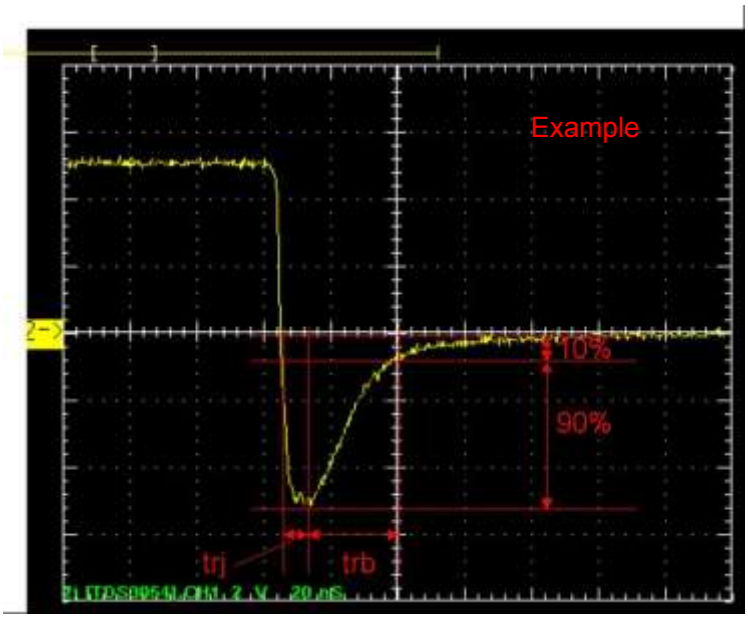
Reverse Recovery Characteristic Reference



Trj= 26.00 (ns)
Trb= 44.00 (ns)
Conditions:Ifwd=Irev=0.2(A),Rl=50



Relation between trj and trb

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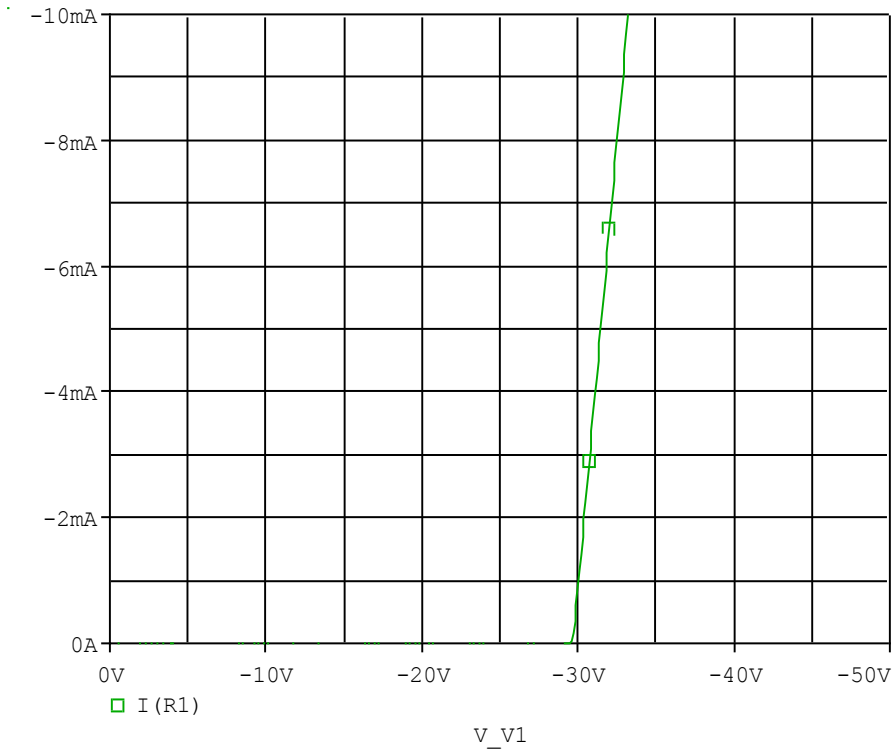
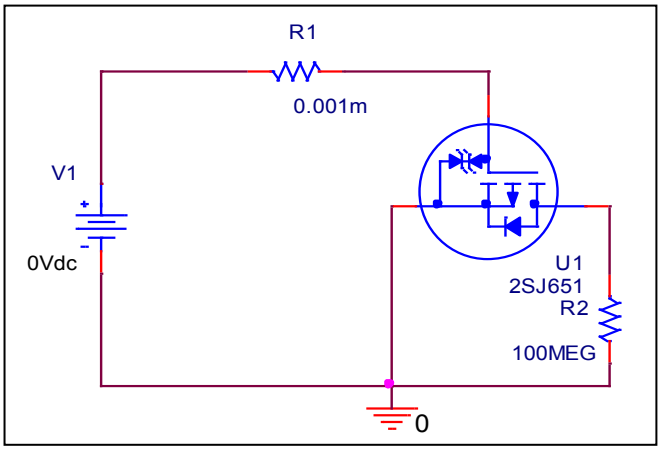
ESD PROTECTION DIODE SPICE MODEL
Zener Voltage Characteristic

Circuit Simulation Result



Evaluation Circuit



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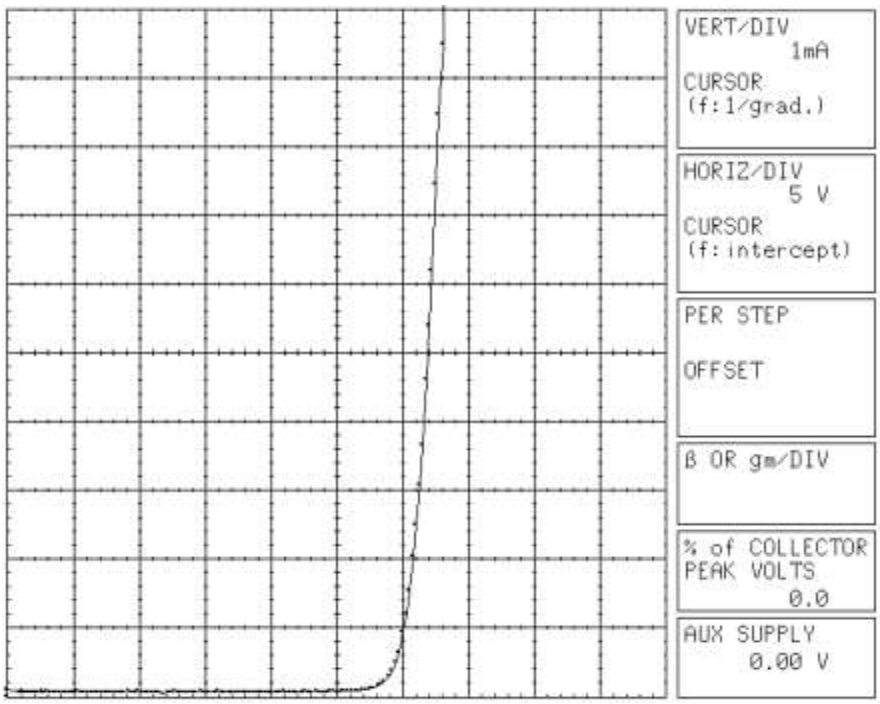
Zener Voltage Characteristic Reference



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